

FEATURES

- 10 μ s Short Circuit Withstand
- High Thermal Cycling Capability
- High Current Density Enhanced DMOS SPT
- Isolated AlSiC Base with AlN Substrates

APPLICATIONS

- Choppers
- Motor Controllers
- Power Supplies
- Traction Auxiliaries

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM250PLM33-TS000 is a 3300V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) chopper module configured with the lower arm of the bridge controlled. The IGBT has a wide reverse bias safe operating area (RBSOA). This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM250PLM33-TS000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	3300V
$V_{CE(sat)}$ * (typ)	2.2V
I_C (max)	250A
$I_{C(PK)}$ (max)	500A

* Measured at the auxiliary terminals

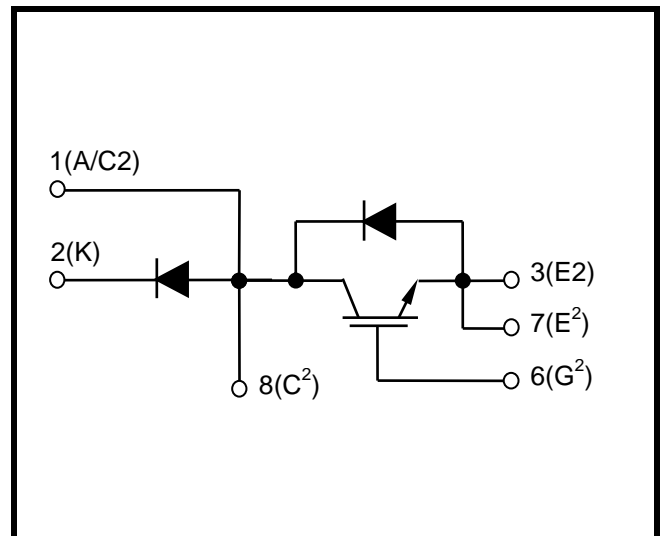
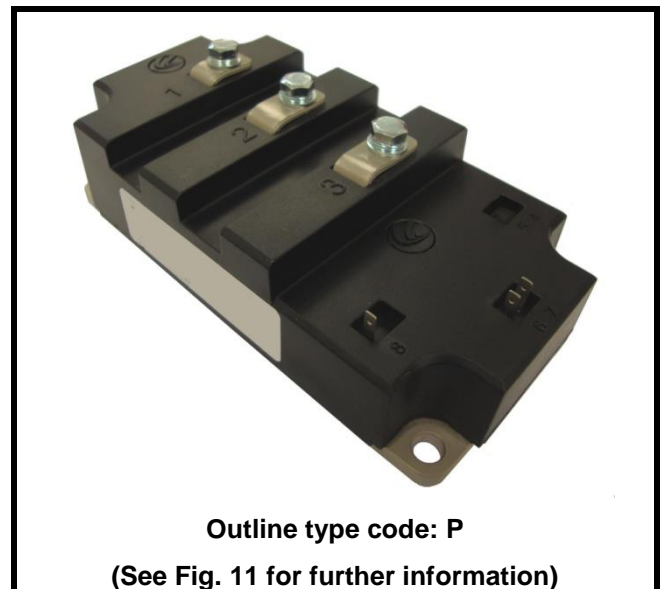


Fig. 1 Circuit configuration



Outline type code: P

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under ‘Absolute Maximum Ratings’ may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V _{CES}	Collector-emitter voltage	V _{GE} = 0V	3300	V
V _{GES}	Gate-emitter voltage		±20	V
I _C	Continuous collector current	T _{case} = 110°C	250	A
I _{C(PK)}	Peak collector current	1ms, T _{case} = 140°C	500	A
P _{max}	Max. transistor power dissipation	T _{case} = 25°C, T _j = 150°C	2.6	kW
I ² t	Diode I ² t value – IGBT Arm	V _R = 0, t _p = 10ms, T _j = 150°C	20	kA ² s
	Diode I ² t value – Diode Arm		20	kA ² s
V _{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	6000	V
Q _{PD}	Partial discharge – per module	IEC1287, V ₁ = 3500V, V ₂ = 2600V, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
R _{th(j-c)}	Thermal resistance – transistor	Continuous dissipation - junction to case	-	-	48	°C/kW
R _{th(j-c)}	Thermal resistance – diode (IGBT Arm)	Continuous dissipation - junction to case	-	-	96	°C/kW
	Thermal resistance – diode (Diode Arm)		-	-	96	°C/kW
R _{th(c-h)}	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	16	°C/kW
T _j	Junction temperature	Transistor	-	-	150	°C
		Diode	-	-	150	°C
T _{stg}	Storage temperature range	-	-40	-	125	°C
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M5	-	-	4	Nm

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector cut-off current	$V_{GE} = 0V, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 125^{\circ}C$			15	mA
		$V_{GE} = 0V, V_{CE} = V_{CES}, T_{case} = 150^{\circ}C$			25	mA
I_{GES}	Gate leakage current	$V_{GE} = \pm 20V, V_{CE} = 0V$			1	μA
$V_{GE(TH)}$	Gate threshold voltage	$I_C = 40mA, V_{GE} = V_{CE}$		5.7		V
$V_{CE(sat)}^{\dagger}$	Collector-emitter saturation voltage	$V_{GE} = 15V, I_C = 250A$		2.2		V
		$V_{GE} = 15V, I_C = 250A, T_j = 125^{\circ}C$		2.8		V
		$V_{GE} = 15V, I_C = 250A, T_j = 150^{\circ}C$		3.0		V
I_F	Diode forward current	DC		250		A
I_{FM}	Diode maximum forward current	$t_p = 1ms$		500		A
V_F	Diode forward voltage † (IGBT arm)	$I_F = 250A$		2.4		V
	Diode forward voltage ‡ (Diode arm)			2.5		V
	Diode forward voltage † (IGBT arm)	$I_F = 250A, T_j = 125^{\circ}C$		2.5		V
	Diode forward voltage ‡ (Diode arm)			2.6		V
	Diode forward voltage † (IGBT arm)	$I_F = 250A, T_j = 150^{\circ}C$		2.4		V
	Diode forward voltage ‡ (Diode arm)			2.5		V
C_{ies}	Input capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		45		nF
Q_g	Gate charge	$\pm 15V$ Including external C_{ge}		5		μC
C_{res}	Reverse transfer capacitance	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		1		nF
L_M	Module inductance			40		nH
R_{INT}	Internal transistor resistance			500		$\mu\Omega$
SC_{Data}	Short circuit current, I_{SC}	$T_j = 150^{\circ}C, V_{CC} = 2500V$ $t_p \leq 10\mu s, V_{GE} \leq 15V$ $V_{CE(max)} = V_{CES} - L^* \times di/dt$ IEC 60747-9		950		A

Note:

† Measured at the auxiliary terminals

‡ Measured at the power busbars

* L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
t _{d(off)}	Turn-off delay time	I _C = 250A V _{GE} = ±15V V _{CE} = 1800V R _{g(ON)} = 10Ω R _{g(OFF)} = 10Ω C _{GE} = 56nF L _S ~ 150nH		2700		ns
t _f	Fall time			520		ns
E _{OFF}	Turn-off energy loss			480		mJ
t _{d(on)}	Turn-on delay time			1000		ns
t _r	Rise time			400		ns
E _{ON}	Turn-on energy loss			320		mJ
Q _{rr}	Diode reverse recovery charge	I _F = 250A V _{CE} = 1800V di _F /dt = 700A/μs		180		μC
I _{rr}	Diode reverse recovery current			160		A
E _{rec}	Diode reverse recovery energy			165		mJ

T_{case} = 125°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
t _{d(off)}	Turn-off delay time	I _C = 250A V _{GE} = ±15V V _{CE} = 1800V R _{g(ON)} = 10Ω R _{g(OFF)} = 10Ω C _{GE} = 56nF L _S ~ 150nH		2750		ns
t _f	Fall time			570		ns
E _{OFF}	Turn-off energy loss			540		mJ
t _{d(on)}	Turn-on delay time			1020		ns
t _r	Rise time			420		ns
E _{ON}	Turn-on energy loss			420		mJ
Q _{rr}	Diode reverse recovery charge	I _F = 250A V _{CE} = 1800V di _F /dt = 700A/μs		230		μC
I _{rr}	Diode reverse recovery current			200		A
E _{rec}	Diode reverse recovery energy			280		mJ

T_{case} = 150°C unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
t _{d(off)}	Turn-off delay time	I _C = 250A V _{GE} = ±15V V _{CE} = 1800V R _{g(ON)} = 10Ω R _{g(OFF)} = 10Ω C _{GE} = 56nF L _S ~ 150nH		2800		ns
t _f	Fall time			550		ns
E _{OFF}	Turn-off energy loss			580		mJ
t _{d(on)}	Turn-on delay time			1030		ns
t _r	Rise time			430		ns
E _{ON}	Turn-on energy loss			460		mJ
Q _{rr}	Diode reverse recovery charge	I _F = 250A V _{CE} = 1800V di _F /dt = 700A/μs		270		μC
I _{rr}	Diode reverse recovery current			200		A
E _{rec}	Diode reverse recovery energy			330		mJ

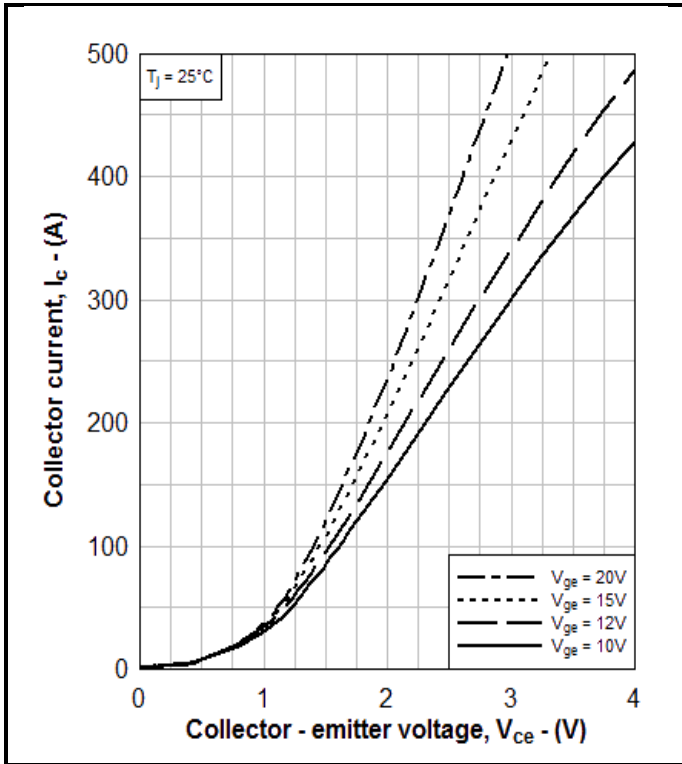


Fig. 3 Typical output characteristics

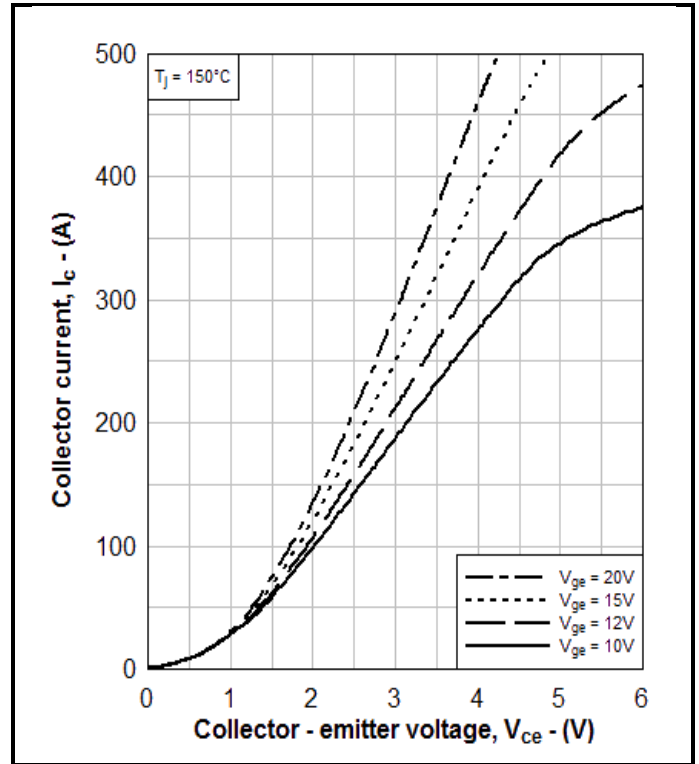


Fig. 4 Typical output characteristics

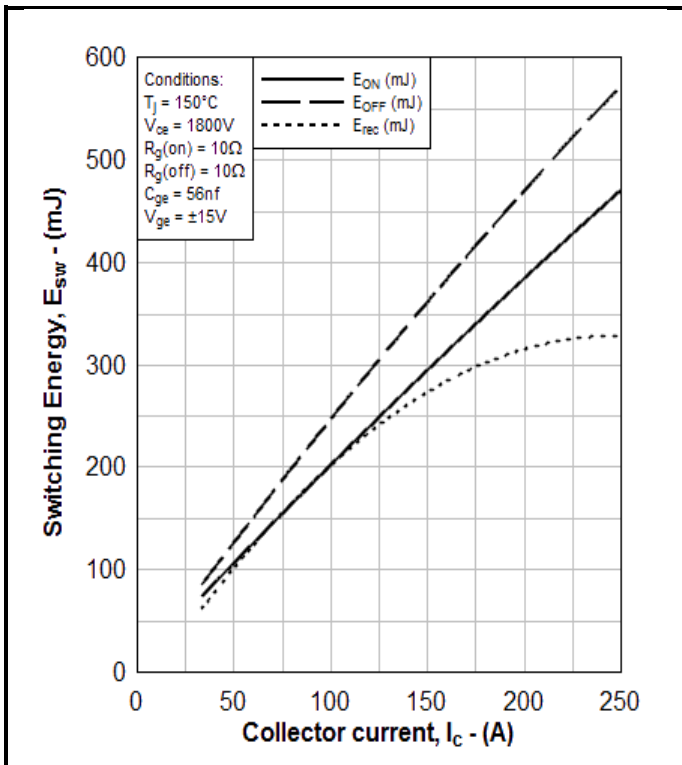


Fig. 5 Typical switching energy vs collector current

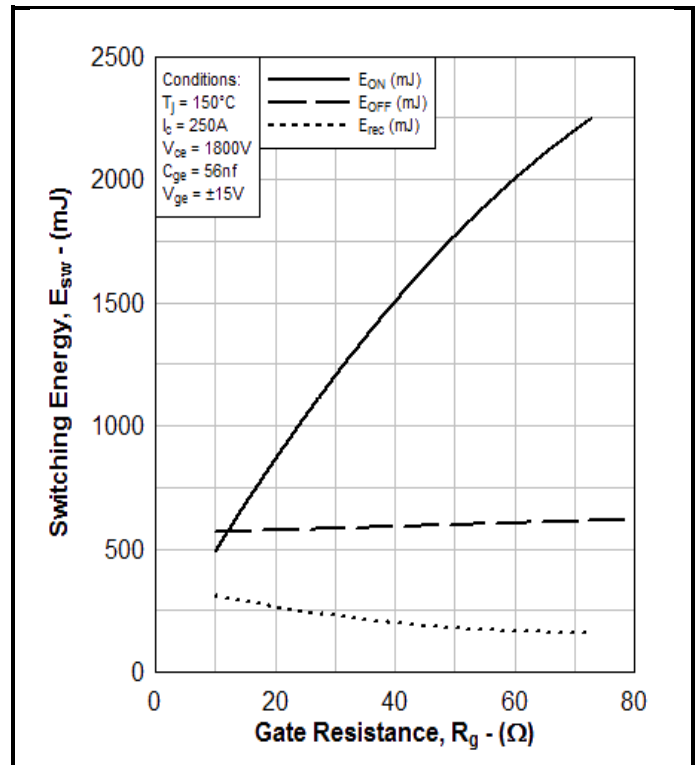


Fig. 6 Typical switching energy vs gate resistance

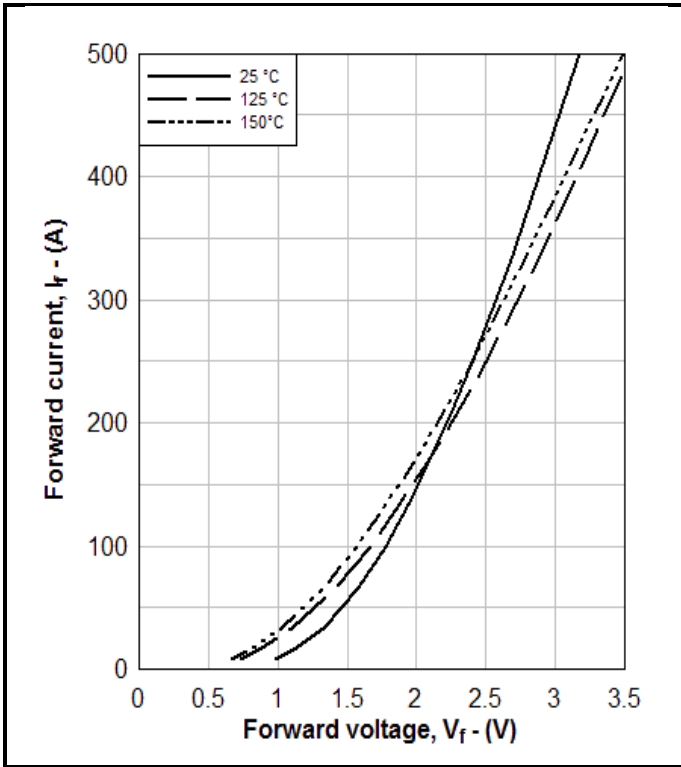


Fig. 7 Diode typical forward characteristics

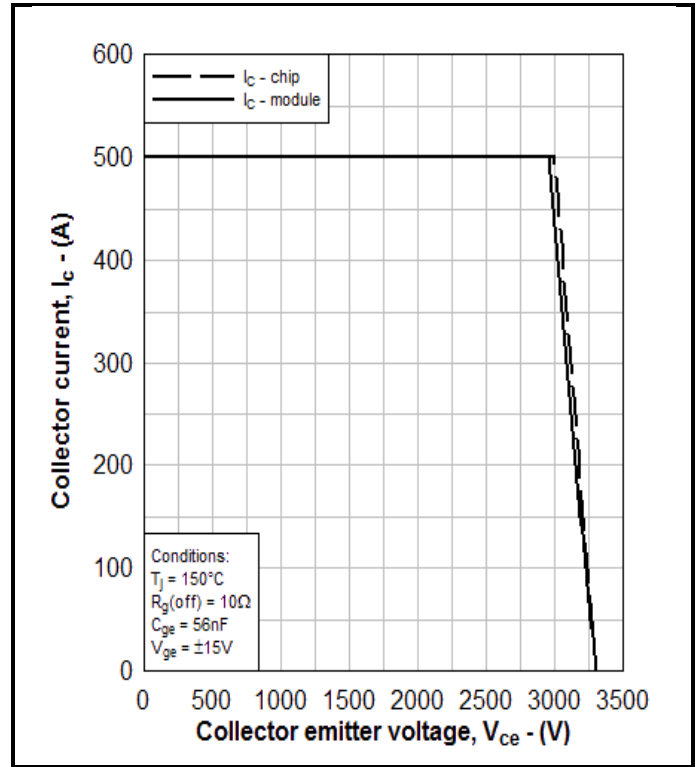


Fig. 8 Reverse bias safe operating area

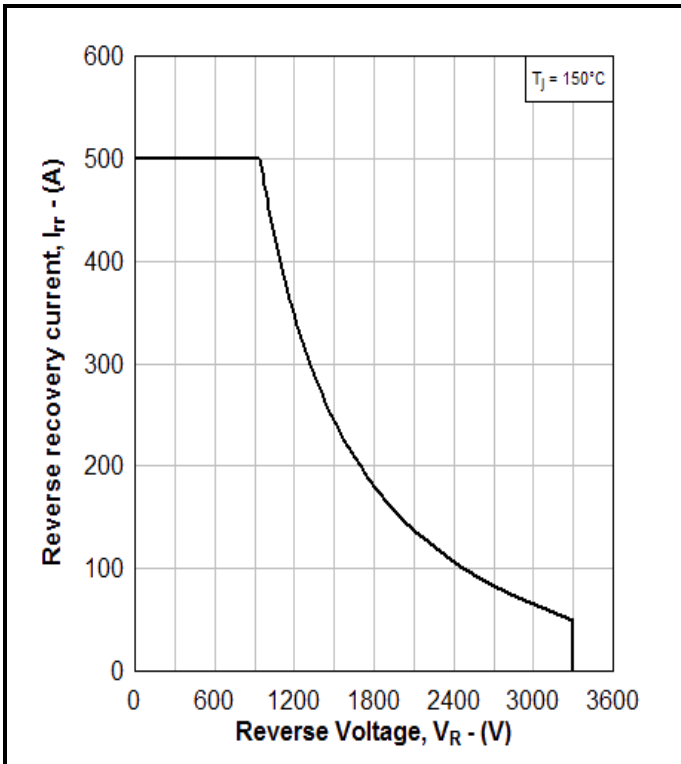


Fig. 9 Diode reverse bias safe operating area

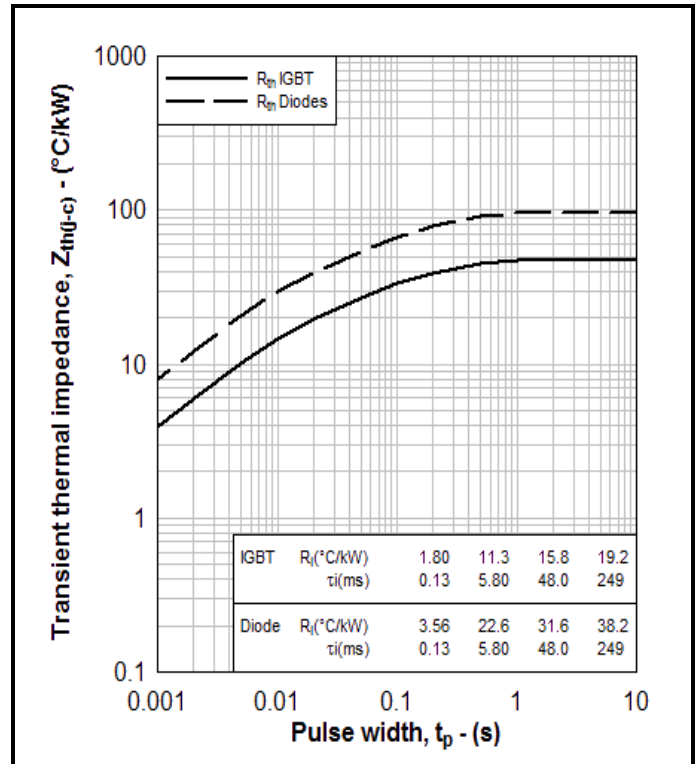


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
All dimensions in mm, unless stated otherwise.
DO NOT SCALE.

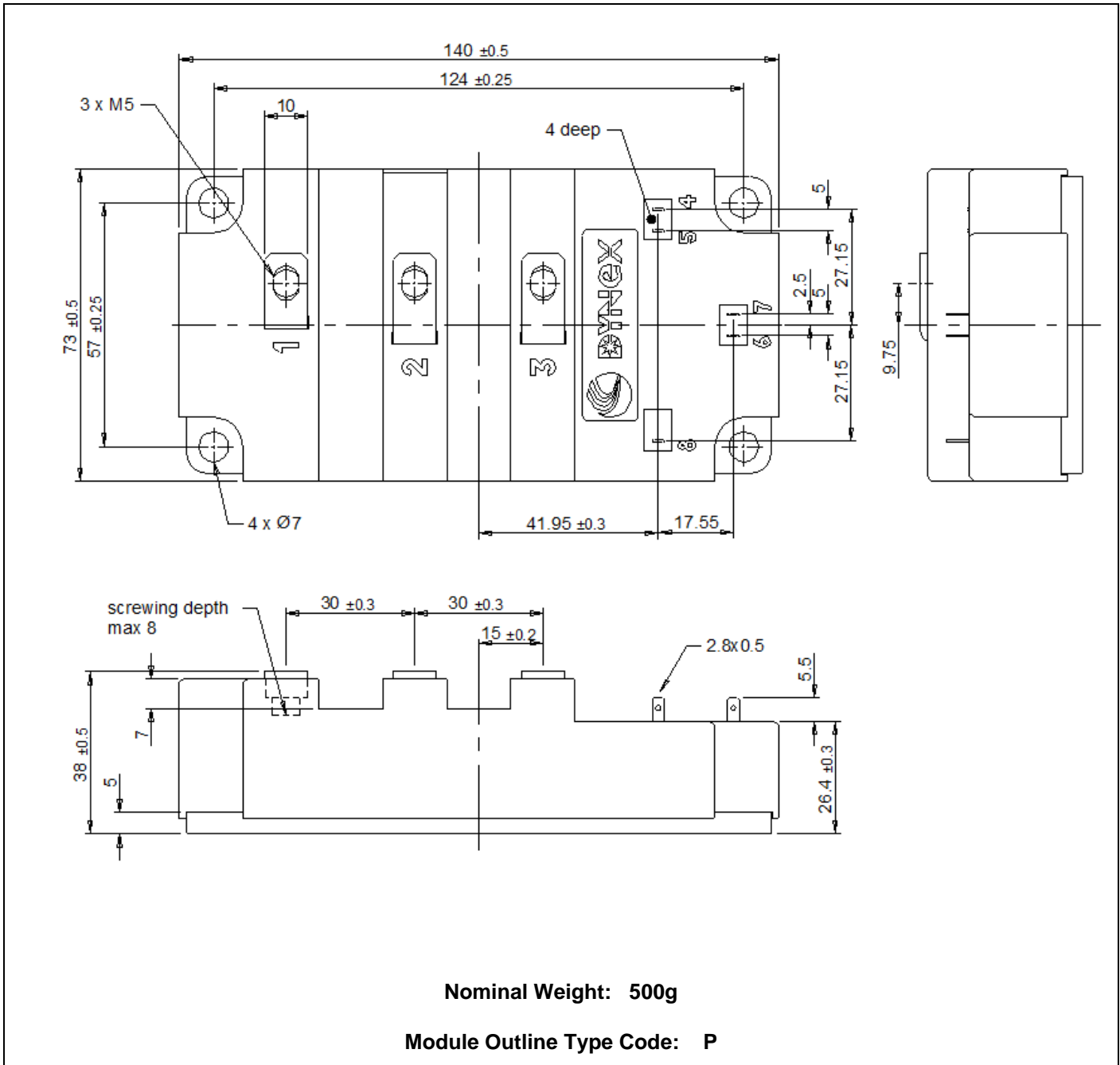


Fig. 11 Module outline drawing

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